# **High Voltage Power Transistors**

# **DPAK for Surface Mount Applications**

Designed for line operated audio output amplifier, switchmode power supply drivers and other switching applications.

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Electrically Similar to Popular MJE340 and MJE350
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

| Rating  | Symbol                            | Max           | Unit      |
|---|-----------------------------------|---------------|-----------|
| Collector-Emitter Voltage   | V <sub>CEO</sub>                  | 300           | Vdc       |
| Collector-Base Voltage  | V <sub>CB</sub>                   | 300           | Vdc       |
| Emitter-Base Voltage  | V <sub>EB</sub>                   | 3             | Vdc       |
| Collector Current – Continuous  | Ic                                | 0.5           | Adc       |
| Collector Current – Peak  | I <sub>CM</sub>                   | 0.75          | Adc       |
| Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C           | P <sub>D</sub>                    | 15<br>0.12    | W<br>W/°C |
| Total Power Dissipation (Note 1)  @ T <sub>A</sub> = 25°C Derate above 25°C | P <sub>D</sub>                    | 1.56<br>0.012 | W<br>W/°C |
| Operating and Storage Junction<br>Temperature Range                         | T <sub>J</sub> , T <sub>stg</sub> | -65 to +150   | °C        |
| ESD – Human Body Model<br>MJD340 (NPN)<br>MJD350 (PNP)                      | НВМ                               | 3B<br>2       | V         |
| ESD – Machine Model<br>MJD340 (NPN)<br>MJD350 (PNP)                         | MM                                | M4<br>M4      | V         |

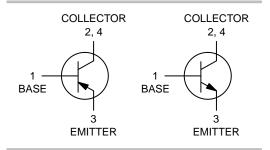
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



#### ON Semiconductor®

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# SILICON **POWER TRANSISTORS** 0.5 AMPERE 300 VOLTS, 15 WATTS





**DPAK CASE 369C** STYLE 1

#### **MARKING DIAGRAM**



= Assembly Location

= Year

WW = Work Week

= Device Code J3x0 x = 4 or 5

= Pb-Free Package

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

<sup>1.</sup> These ratings are applicable when surface mounted on the minimum pad sizes recommended.

#### THERMAL CHARACTERISTICS

| Characteristic                                   | Symbol         | Max  | Unit |
|--|----------------|------|------|
| Thermal Resistance, Junction-to-Case             | $R_{	heta JC}$ | 8.33 | °C/W |
| Thermal Resistance, Junction-to-Ambient (Note 2) | $R_{	heta JA}$ | 80   | °C/W |
| Leading Temperature for Soldering Purpose        | TL             | 260  | °C   |

<sup>2.</sup> These ratings are applicable when surface mounted on the minimum pad sizes recommended.

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

| Characteristic   | Symbol                | Min | Max | Unit |
|--|-----------------------|-----|-----|------|
| OFF CHARACTERISTICS  |                       | •   |     | 1    |
| Collector–Emitter Sustaining Voltage (Note 3) (I <sub>C</sub> = 1 mA, I <sub>B</sub> = 0)        | V <sub>CEO(sus)</sub> | 300 | _   | V    |
| Collector Cutoff Current (V <sub>CB</sub> = 300 V, I <sub>E</sub> = 0)                           | I <sub>CEO</sub>      | -   | 0.1 | mA   |
| Emitter Cutoff Current $(V_{BE} = 3 \text{ V, } I_{C} = 0)$                                      | I <sub>EBO</sub>      | _   | 0.1 | mA   |
| ON CHARACTERISTICS (Note 3)  | •                     |     |     |      |
| DC Current Gain<br>(I <sub>C</sub> = 50 mA, V <sub>CE</sub> = 10 V)                              | h <sub>FE</sub>       | 30  | 240 | _    |
| Collector–Emitter Saturation Voltage (I <sub>C</sub> = 100 mA, I <sub>B</sub> = 10 mA)           | V <sub>CE(sat)</sub>  | _   | 1   | V    |
| Base–Emitter On Voltage<br>(I <sub>C</sub> = 1 A, V <sub>CE</sub> = 10 V)                        | V <sub>BE(on)</sub>   | -   | 1.5 | V    |
| DYNAMIC CHARACTERISTICS  | •                     | •   | •   | •    |
| Current Gain – Bandwidth Product<br>(I <sub>C</sub> = 50 mA, V <sub>CE</sub> = 10 V, f = 10 MHz) | f <sub>T</sub>        | 10  | _   | MHz  |
|  |                       |     |     |      |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%.

## **TYPICAL CHARACTERISTICS**

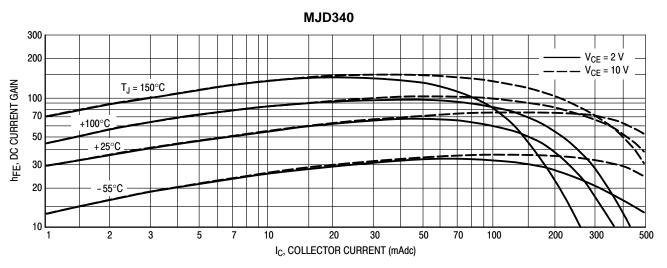


Figure 1. DC Current Gain

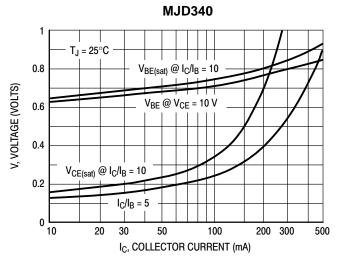
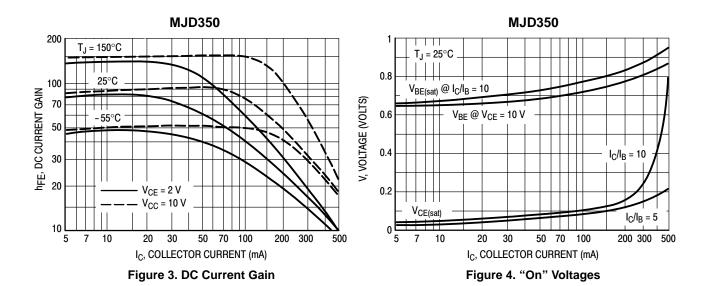


Figure 2. "On" Voltages



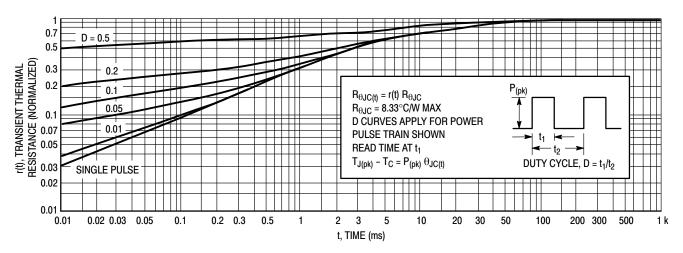


Figure 5. Thermal Response

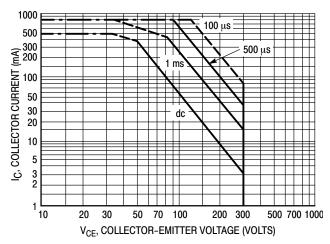


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

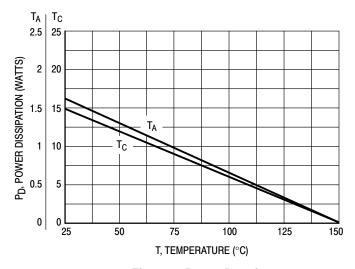


Figure 7. Power Derating

### **ORDERING INFORMATION**

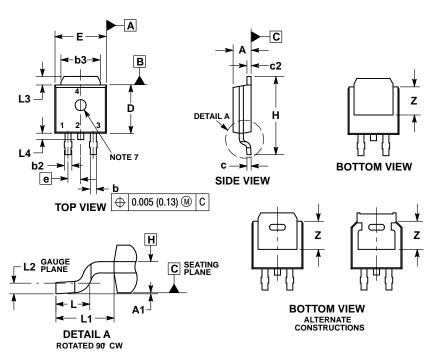
| Device       | Package           | Shipping <sup>†</sup> |
|--------------|-------------------|-----------------------|
| MJD340G      | DPAK<br>(Pb-Free) | 75 Units / Rail       |
| MJD340RLG    | DPAK<br>(Pb-Free) | 1,800 / Tape & Reel   |
| MJD340T4G    | DPAK<br>(Pb-Free) | 2,500 / Tape & Reel   |
| NJVMJD340T4G | DPAK<br>(Pb-Free) | 2,500 / Tape & Reel   |
| MJD350G      | DPAK<br>(Pb-Free) | 75 Units / Rail       |
| MJD350T4G    | DPAK<br>(Pb-Free) | 2,500 / Tape & Reel   |
| NJVMJD350T4G | DPAK<br>(Pb-Free) | 2,500 / Tape & Reel   |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

## **DPAK (SINGLE GAUGE)**

CASE 369C ISSUE F



#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
- CONTROLLING DIMENSION: INCHES.
  THERMAL PAD CONTOUR OPTIONAL WITHIN DI-MENSIONS b3, L3 and Z.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
  5. DIMENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.
  6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE

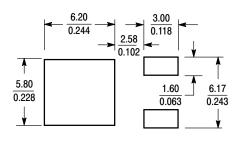
|     | INCHES    |       | MILLIMETERS |       |
|-----|-----------|-------|-------------|-------|
| DIM | MIN       | MAX   | MIN         | MAX   |
| Α   | 0.086     | 0.094 | 2.18        | 2.38  |
| A1  | 0.000     | 0.005 | 0.00        | 0.13  |
| b   | 0.025     | 0.035 | 0.63        | 0.89  |
| b2  | 0.028     | 0.045 | 0.72        | 1.14  |
| b3  | 0.180     | 0.215 | 4.57        | 5.46  |
| С   | 0.018     | 0.024 | 0.46        | 0.61  |
| c2  | 0.018     | 0.024 | 0.46        | 0.61  |
| D   | 0.235     | 0.245 | 5.97        | 6.22  |
| Е   | 0.250     | 0.265 | 6.35        | 6.73  |
| е   | 0.090 BSC |       | 2.29 BSC    |       |
| Н   | 0.370     | 0.410 | 9.40        | 10.41 |
| L   | 0.055     | 0.070 | 1.40        | 1.78  |
| L1  | 0.114 REF |       | 2.90 REF    |       |
| L2  | 0.020 BSC |       | 0.51 BSC    |       |
| L3  | 0.035     | 0.050 | 0.89        | 1.27  |
| L4  |           | 0.040 |             | 1.01  |
| Z   | 0.155     |       | 3.93        |       |

#### STYLE 1:

- PIN 1. BASE 2. COLLECTOR

  - EMITTER COLLECTOR

#### **SOLDERING FOOTPRINT\***



(mm inches SCALE 3:1

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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